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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO		
10/600,886	06/19/2003	Dror Shemesh	PDC/7822	5920		
7590 05/05/2004			EXAMINER			
PATENT COUNSEL			HASHMI, ZIA R			
APPLIED MA Legal Affairs I	TERIALS, INC. Department	ART UNIT	PAPER NUMBER			
P.O. BOX 450A			2881			
Santa Clara, CA 95052			DATE MAILED: 05/05/2004			

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Арі	olication No.		Applicant(s)		7		
			600,886		SHEMESH, DROP	₹			
Office Action Summary		Exa	min r		Art Unit				
		Zia	R. Hashmi		2881				
 Period for	The MAILING DATE of this communi Reply	cation appears	on the cover sheet	t with th	orrespondenc ad	dress	_		
THE M Extensi after SI - If the pi - If NO pi - Failure Any rep	RTENED STATUTORY PERIOD FOR AILING DATE OF THIS COMMUNITIONS of time may be available under the provisions of time may be available under the provisions of X (6) MONTHS from the mailing date of this commercial for reply specified above is less than thirty (30 period for reply is specified above, the maximum state to reply within the set or extended period for reply only received by the Office later than three months all patent term adjustment. See 37 CFR 1.704(b).	CATION. of 37 CFR 1.136(a). unication. of days, a reply within tutory period will app will, by statute, cause	In no event, however, may the statutory minimum of y and will expire SIX (6) N the application to become	y a reply be time f thirty (30) days MONTHS from the BANDONED	ely filed will be considered timel he mailing date of this of				
Status									
1)⊠ F	Responsive to communication(s) file	d on <i>19 June 2</i>	003.						
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<i>,</i> —	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.								
Dispositio	n of Claims								
5)☐ C 6)☒ C 7)☐ C 8)☐ C Applicatio 9)☐ T 10)☒ T	Claim(s) 1-38 is/are pending in the a a) Of the above claim(s) is/are Claim(s) is/are allowed. Claim(s) 1-38 is/are rejected. Claim(s) is/are objected to. Claim(s) is/are objected to restrice The Papers The specification is objected to by the drawing(s) filed on 19 June 2003 Applicant may not request that any objected to applicant may not request the applicant may not request the applicant may not request the applicant may	tion and/or elected by the Examiner.	ction requirement. ccepted or b)□ o	bjected to t	-				
	Replacement drawing sheet(s) including the oath or declaration is objected to		•).		
Priority un	der 35 U.S.C. § 119					-			
a)	cknowledgment is made of a claim of a laim of all b) Some * c) None of: Certified copies of the priority of the certified copies of the priority of the certified copies of application from the Internation of the attached detailed Office actions.	documents hav documents hav of the priority d nal Bureau (PC	re been received. re been received in ocuments have be cT Rule 17.2(a)).	n Applicatio	on No d in this National	Stage			
Attachment(s	•		"□		DTO 440				
2) Notice 3) Informa	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (P ation Disclosure Statement(s) (PTO-1449 or No(s)/Mail Date	•	Paper I			O-152)			

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-38 are rejected under U.S.C. 103(a) as being unpatentable over Sievers et al. (US 2002/0195422 A1), in view of Winters et al. (4,226,666).
- 3. With respect to independent claims 1, 12, 23 and 32, Sievers et al. disclose a method and apparatus of reducing or removal of ion contamination in an object, the ion contamination introduced by an ion milling step (Abstract, line 1, para 0004, lines 1-2, para 0003, lines 9-13, and para 0005, lines 1-3), comprising the steps of defining a suspected ion contaminated area (para 0015, lines 1-12), removing the suspected ion contaminated area by an ion beam (para 0001, lines 3-6, para 0004, lines 5-7, para 0005, lines 3-7, and para 0009, lines 6-10). Their method is also applicable to milling an integrated circuit by a rapid milling process (para 0015, lines 9-12).
- 4. With respect to dependent claims 2, 7, 13, 18, 24, 29, and 33, Sievers et al. disclose a method and apparatus where the ion beam consists of Gallium metal ions (para 0018, lines 1-2) and wherein the object is an integrated circuit (para 0001, lines 3-6, para 0015, lines 9-12).
- 5. With respect to claims 1, 3-6, 8-12, 14-17, 19-23, 25-28, 30-32, and 34-38, Sievers et al. fail to disclose use of a non-contaminating process (such as directing

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an electron beam toward the removed area while allowing the beam to interact with additional material). Winters et al., however, disclose a method and apparatus for removing any area on a substrate, which can be removed by electron beam etching (col. 1, lines 15-20, col. 2, lines 41-48 & 59-64, col. 3, lines 3-10, col. 4, lines 13-16, and Fig. 1-3), which is a non-contaminating process since the electron beam does not introduce any external contaminating ions. Thus, the use of electron beam to remove or etch out undesired areas on a surface of substrate of a semiconductor is a well known practice (col. 1, lines 15-27) in semiconductor manufacturing industry.

It would have been obvious to one having ordinary skill in the art at the time of the invention was made to combine the methods and apparatus of Sievers and Winters et al. and add features like defining a suspected contaminated area and removing it in one step within the fabrication or inspection process of the substrate, because Sievers et al. teach (para 0001, lines 3-6) that in the fabrication of integrated circuits, focused ion beam is frequently used to mill away (etch) material by irradiating an ion beam onto a substrate.

Conclusion

- 5. DeMarco et al. disclose (5,288,368) direct-writing electron beam apparatus, which not only can be used for writing patterns on a substrate, but also removing entire thickness of a layer on it.
- 6. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published

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applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact Electronic Business Center (EBC) at 866-217-9197 (toll-free).

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Zia Hashmi whose telephone number is (571) 272-2473. The examiner can normally be reached between 8.30 AM- 5 PM. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John R. Lee can be reached on (571) 272-2477.

Zia Hashmi

April 21, 2004.

JOHN R. LFF

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SUPPLAVISORY PATEUT SUCCESS